

N-Channel MOSFET Transistor

2SK214 / K214

160V / 0.5A

DATASHEET

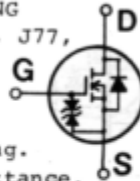
OEM – Hitachi

Source: Hitachi Databook Power Mosfet Data 4/83

2SK213, 2SK214, 2SK215, 2SK216

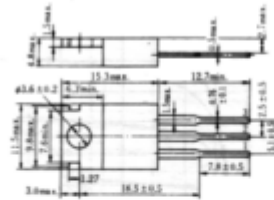
SILICON N-CHANNEL MOS FET

HIGH FREQUENCY AND LOW FREQUENCY POWER AMPLIFIER, HIGH SPEED SWITCHING
Complementary Pair with 2SJ76, J77, J78, J79



Features;

- Suitable for Direct Mounting.
- High Forward Transfer Admittance.
- Excellent Frequency Response.
- Enhancement-Mode.



(Dimensions in mm)
(JEDEC TO-220AB)

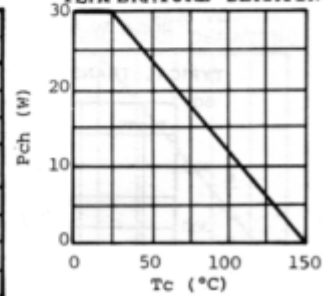
1. Gate
2. Source (Flange)
3. Drain

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	Ratings				Unit
		K213	K214	K215	K216	
Drain-Source Voltage	V _{DSX}	140	160	180	200	V
Gate-Source Voltage	V _{GSS}	±15				V
Drain Current	I _D	500				mA
Body-Drain Diode Reverse Drain Current	I _{DR}	500				mA
Channel Dissipation	P _{ch}	1.75				W
	P _{ch} *	30				W
Channel Temperature	T _{ch}	150				°C
Storage Temperature	T _{stg}	-45 ~ +150				°C

*Value at Tc=25°C

POWER VS. TEMPERATURE DERATING



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Drain-Source Breakdown Voltage	K213	I _D =1mA, V _{GS} =-2V	140	-	-	V
	K214		160	-	-	V
	K215		180	-	-	V
	K216		200	-	-	V
Gate-Source Breakdown Voltage	V _{(BR)GSS}	I _G =±10μA, V _{DS} =0	±15	-	-	V
Gate-Source Voltage	V _{GS(on)}	I _D =10mA, V _{DS} =10V*	0.2	-	1.5	V
Drain-Source Saturation Voltage	V _{DS(sat)}	I _D =10mA, V _{GD} =0 *	-	-	2.0	V
Forward Transfer Admittance	y _{fs}	I _D =10mA, V _{DS} =20V*	-	40	-	mS
Input Capacitance	C _{iss}	I _D =10mA, V _{DS} =10V, f=1MHz	-	90	-	pF
Reverse Transfer Capacitance	C _{rss}		-	2.2	-	pF



2SK213,2SK214,2SK215,2SK216

